

Serial No. 09/856,212

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IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-8 (cancelled)

9. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~characterized in comprising the steps of that~~ maintaining a heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment ~~is at less than 500°C or less,~~ and maintaining a temperature ramping rate in a temperature range from the heat treatment temperature at initial entry to an ~~ultimate a maximum~~ temperature ~~set in a range of 700°C - 900°C,~~ is set to said ramping rate being 1°C/min or less.

10. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~characterized in comprising the steps of that~~ maintaining a heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment ~~is at less than 500°C or less,~~ and maintaining a temperature ramping rate in a temperature range from the heat treatment temperature at initial entry to an ~~ultimate a maximum~~ temperature ~~set in a range of 700°C - 900°C,~~ said ramping rate being is set to 1°C/min or less, so as to make uniform the distribution of an oxide precipitate density of the silicon single crystal wafer after heat treatment.

11. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, comprising the steps of ~~characterized in that~~ acontrolling heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment and controlling a temperature ramping rate from the heat treatment